

# NTD14N03R, NVD14N03R

## Power MOSFET

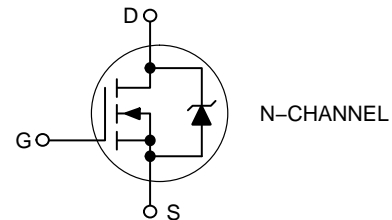
14 A, 25 V, N-Channel DPAK



ON Semiconductor®

[www.onsemi.com](http://www.onsemi.com)

14 AMPERES, 25 VOLTS  
 $R_{DS(on)} = 70.4 \text{ m}\Omega$  (Typ)



### Features

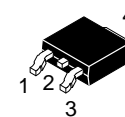
- Planar HD3e Process for Fast Switching Performance
- Low  $R_{DS(on)}$  to Minimize Conduction Loss
- Low  $C_{iss}$  to Minimize Driver Loss
- Low Gate Charge
- Optimized for High Side Switching Requirements in High-Efficiency DC-DC Converters
- NVD and SVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	25	Vdc
Gate-to-Source Voltage – Continuous	$V_{GS}$	$\pm 20$	Vdc
Thermal Resistance – Junction-to-Case	$R_{\theta JC}$	6.0	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	20.8	W
Drain Current – Continuous @ $T_A = 25^\circ\text{C}$ , Chip	$I_D$	14	A
– Continuous @ $T_A = 25^\circ\text{C}$ , Limited by Package	$I_D$	11.4	A
– Single Pulse ( $t_p \leq 10 \mu\text{s}$ )	$I_D$	28	A
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	80	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	1.56	W
Drain Current – Continuous @ $T_A = 25^\circ\text{C}$	$I_D$	3.1	A
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	120	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	1.04	W
Drain Current – Continuous @ $T_A = 25^\circ\text{C}$	$I_D$	2.5	A
Operating and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	$T_L$	260	$^\circ\text{C}$

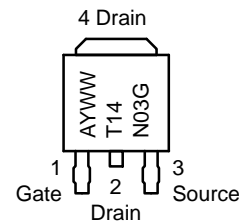
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. When surface mounted to an FR4 board using 0.5 sq. in pad size.
2. When surface mounted to an FR4 board using minimum recommended pad size.



DPAK  
CASE 369C  
(Surface Mount)  
STYLE 2

### MARKING DIAGRAM & PIN ASSIGNMENTS



A = Assembly Location\*  
Y = Year  
WW = Work Week  
14N03 = Device Code  
G = Pb-Free Package

\* The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package, the front side assembly code may be blank.

### ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

# NTD14N03R, NVD14N03R

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage (Note 3) (V <sub>GS</sub> = 0 Vdc, I <sub>D</sub> = 250 μAdc) Temperature Coefficient (Positive)	V <sub>(br)DSS</sub>	25 –	28 –	– –	Vdc mV/°C
Zero Gate Voltage Drain Current (V <sub>DS</sub> = 20 Vdc, V <sub>GS</sub> = 0 Vdc) (V <sub>DS</sub> = 20 Vdc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 150°C)	I <sub>DSS</sub>	– –	– –	1.0 10	μAdc
Gate-Body Leakage Current (V <sub>GS</sub> = ±20 Vdc, V <sub>DS</sub> = 0 Vdc)	I <sub>GSS</sub>	–	–	±100	nAdc

### ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage (Note 3) (V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μAdc) Threshold Temperature Coefficient (Negative)	V <sub>GS(th)</sub>	1.0 –	1.5 –	2.0 –	Vdc mV/°C
Static Drain-to-Source On-Resistance (Note 3) (V <sub>GS</sub> = 4.5 Vdc, I <sub>D</sub> = 5 Adc) (V <sub>GS</sub> = 10 Vdc, I <sub>D</sub> = 5 Adc)	R <sub>DS(on)</sub>	– –	117 70.4	130 95	mΩ
Forward Transconductance (Note 3) (V <sub>DS</sub> = 10 Vdc, I <sub>D</sub> = 5 Adc)	g <sub>FS</sub>	–	7.0	–	Mhos

### DYNAMIC CHARACTERISTICS

Input Capacitance	(V <sub>DS</sub> = 20 Vdc, V <sub>GS</sub> = 0 V, f = 1 MHz)	C <sub>iss</sub>	–	115	–	pF
Output Capacitance		C <sub>oss</sub>	–	62	–	
Transfer Capacitance		C <sub>rss</sub>	–	33	–	

### SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	(V <sub>GS</sub> = 10 Vdc, V <sub>DD</sub> = 10 Vdc, I <sub>D</sub> = 5 Adc, R <sub>G</sub> = 3 Ω)	t <sub>d(on)</sub>	–	3.8	–	ns
Rise Time		t <sub>r</sub>	–	27	–	
Turn-Off Delay Time		t <sub>d(off)</sub>	–	9.6	–	
Fall Time		t <sub>f</sub>	–	2.0	–	
Gate Charge	(V <sub>GS</sub> = 5 Vdc, I <sub>D</sub> = 5 Adc, V <sub>DS</sub> = 10 Vdc) (Note 3)	Q <sub>T</sub>	–	1.8	–	nC
		Q <sub>1</sub>	–	0.8	–	
		Q <sub>2</sub>	–	0.7	–	

### SOURCE-DRAIN DIODE CHARACTERISTICS

Forward On-Voltage	(I <sub>S</sub> = 5 Adc, V <sub>GS</sub> = 0 Vdc) (Note 3) (I <sub>S</sub> = 5 Adc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 125°C)	V <sub>SD</sub>	– –	0.93 0.82	1.2 –	Vdc
Reverse Recovery Time	(I <sub>S</sub> = 5 Adc, V <sub>GS</sub> = 0 Vdc, di <sub>S</sub> /dt = 100 A/μs) (Note 3)	t <sub>rr</sub>	–	6.6	–	ns
		t <sub>a</sub>	–	4.75	–	
		t <sub>b</sub>	–	1.88	–	
Reverse Recovery Stored Charge		Q <sub>RR</sub>	–	0.002	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

4. Switching characteristics are independent of operating junction temperatures.

# NTD14N03R, NVD14N03R

## TYPICAL CHARACTERISTICS

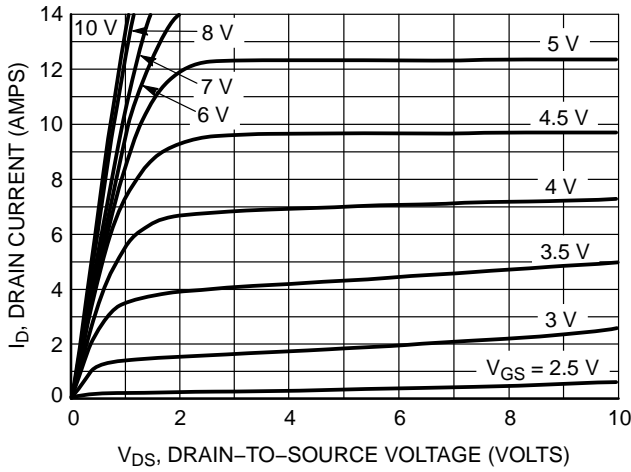


Figure 1. On-Region Characteristics

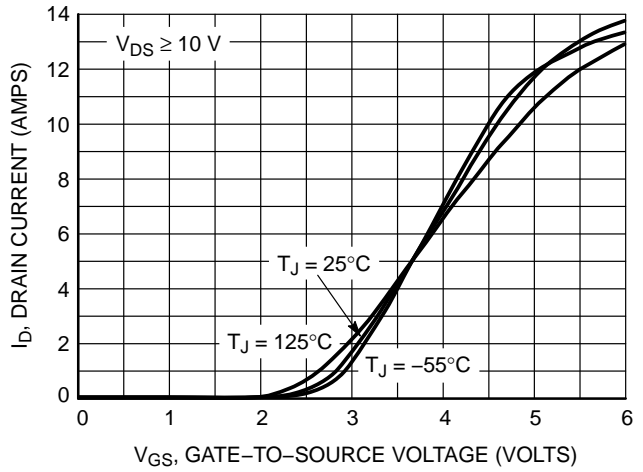


Figure 2. Transfer Characteristics

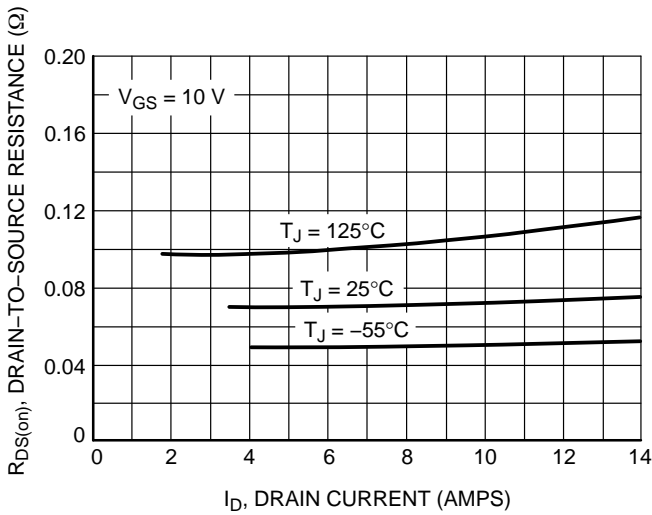


Figure 3. On-Resistance versus Drain Current and Temperature

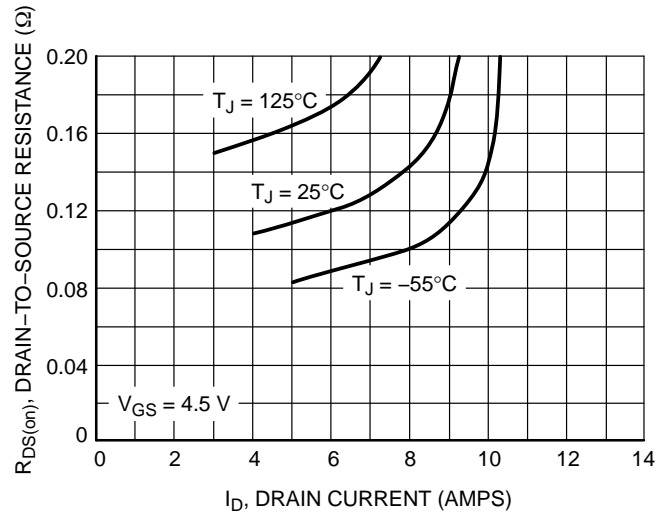


Figure 4. On-Resistance versus Drain Current and Temperature

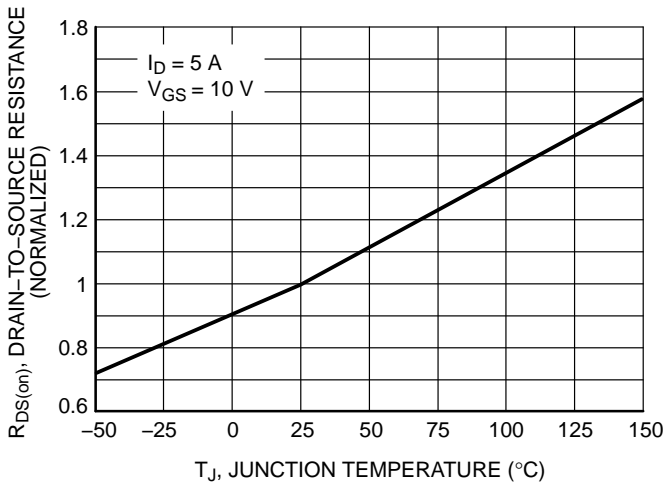


Figure 5. On-Resistance Variation with Temperature

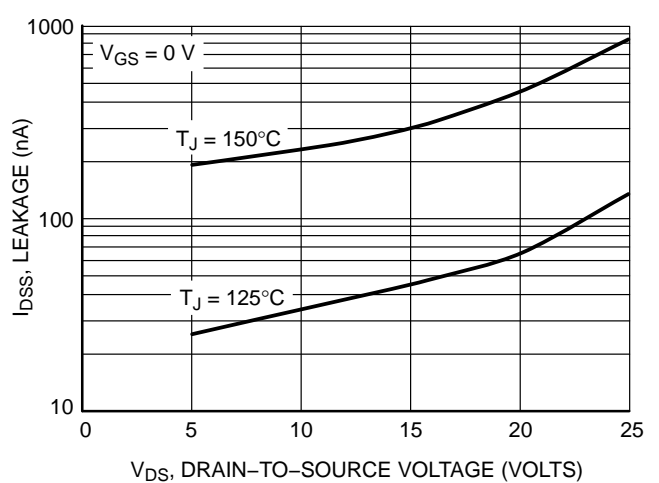


Figure 6. Drain-to-Source Leakage Current versus Voltage

# NTD14N03R, NVD14N03R

## TYPICAL CHARACTERISTICS

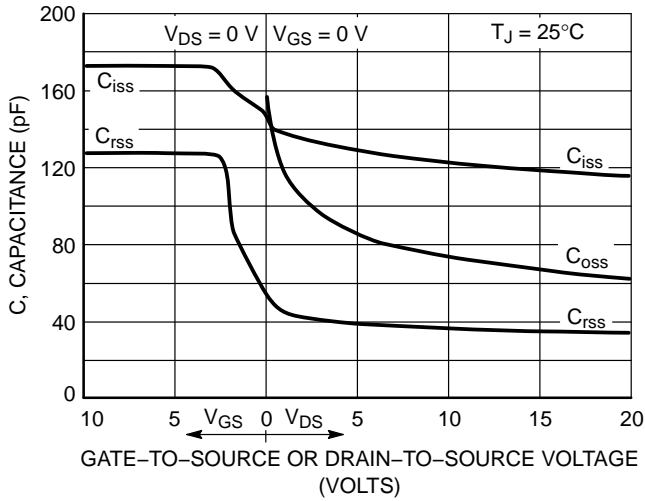


Figure 7. Capacitance Variation

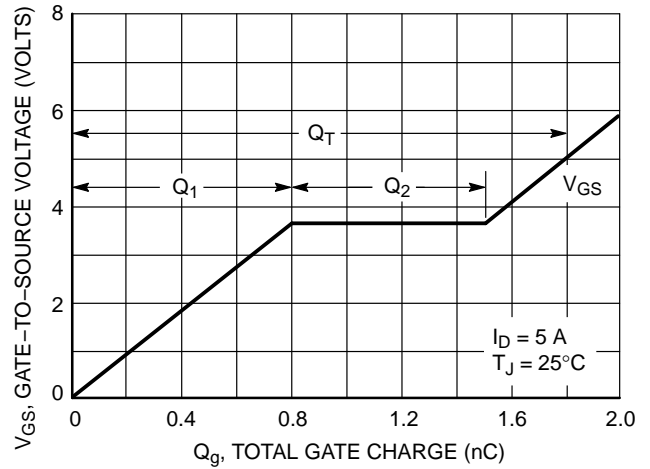


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

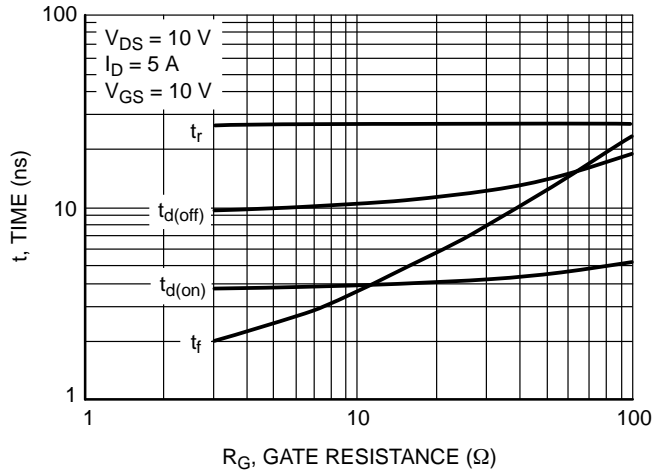


Figure 9. Resistive Switching Time Variation versus Gate Resistance

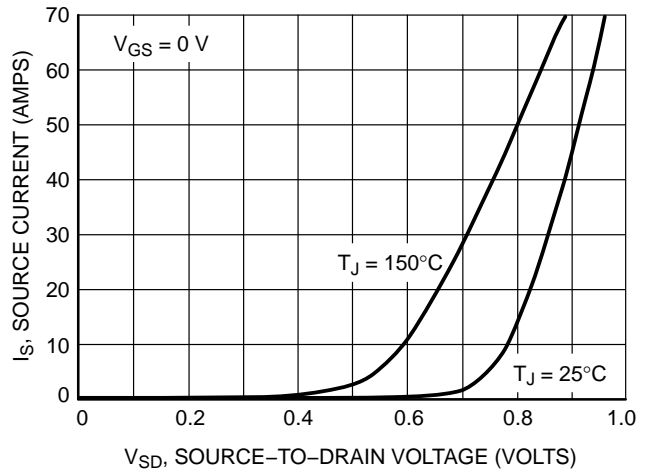


Figure 10. Diode Forward Voltage versus Current

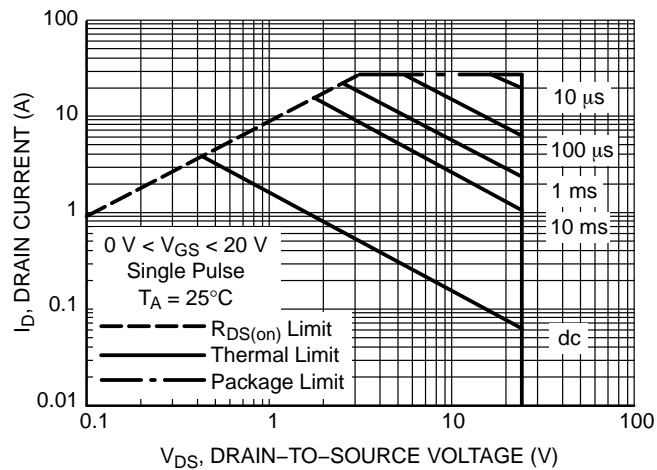


Figure 11. Maximum Rated Forward Biased Safe Operating Area

# NTD14N03R, NVD14N03R

## TYPICAL CHARACTERISTICS

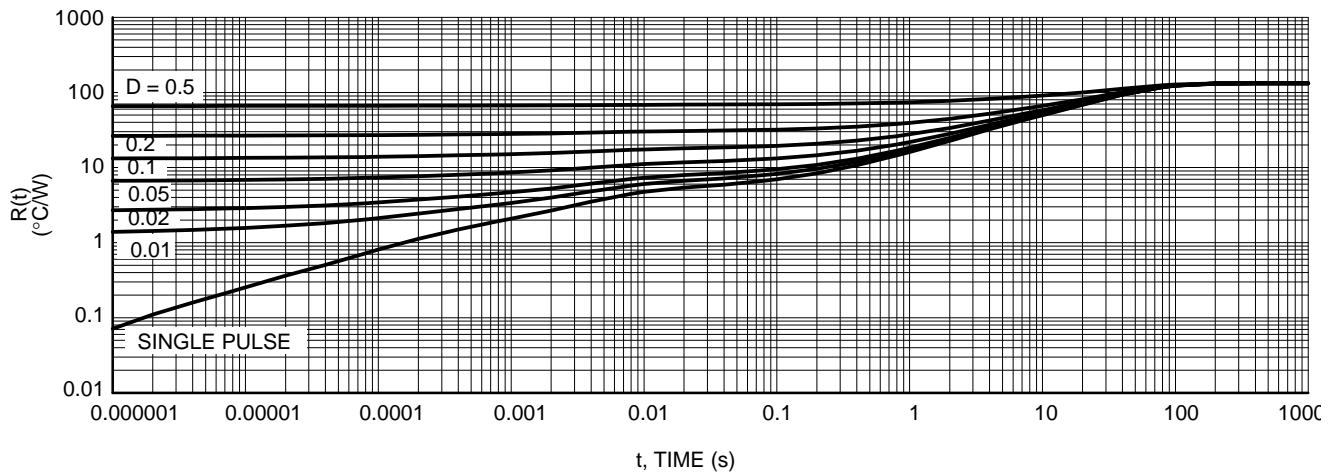


Figure 12. Thermal Response

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NTD14N03RT4G	DPAK (Pb-Free)	2500 / Tape & Reel
NVD14N03RT4G*	DPAK (Pb-Free)	2500 / Tape & Reel
SVD14N03RT4G*	DPAK (Pb-Free)	2500 / Tape & Reel

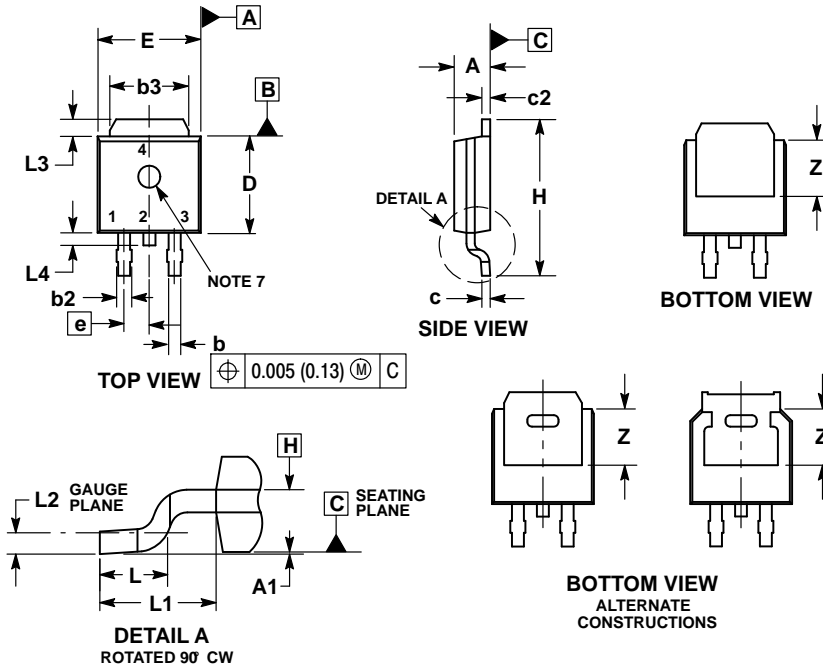
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NVD and SVD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

# NTD14N03R, NVD14N03R

## PACKAGE DIMENSIONS

### DPAK (SINGLE GAUGE) CASE 369C ISSUE F



#### NOTES:

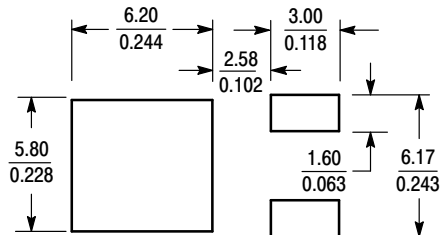
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29	BSC
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020	BSC	0.51	BSC
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

#### STYLE 2:

1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

#### SOLDERING FOOTPRINT\*



SCALE 3:1 (mm/inches)

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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